

Product data sheet

Unit А

А

А

А

V

V

V

ns

ns

ns

## 1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

## 2. Features and benefits

- Isolated plastic package
- Low reverse recovery current
- Low thermal resistance •
- Reduces switching losses in associated MOSFET .

## 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC) •
- Half-bridge/full-bridge switched-mode power supplies •
- Half-bridge lighting ballasts

## 4. Quick reference data

| Symbol             | Parameter                           | Conditions  | Min | Тур | Max  |
|--------------------|-------------------------------------|---|-----|-----|------|
| I <sub>F(AV)</sub> | average forward current             | δ = 0.5 ; T <sub>h</sub> ≤ 59 °C; square-wave<br>pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>   | -   | -   | 8    |
| I <sub>FRM</sub>   | repetitive peak forward current     | δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>h</sub> ≤ 59 °C; square-wave pulse   | -   | -   | 16   |
| I <sub>FSM</sub>   | non-repetitive peak forward current | t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave<br>pulse  | -   | -   | 80   |
|                    |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse  | -   | -   | 88   |
| Static chara       | acteristics                         |   |     |     |      |
| V <sub>F</sub>     | forward voltage                     | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>  | -   | 1.4 | 1.85 |
|                    |                                     | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C  | -   | 2   | 2.9  |
|                    |                                     | I <sub>F</sub> = 16 A; T <sub>j</sub> = 150 °C  | -   | 1.7 | 2.3  |
| Dynamic ch         | naracteristics                      | · · · · ·   |     |     |      |
| t <sub>rr</sub>    | reverse recovery time               | $ I_{F} = 8 \text{ A}; \text{ V}_{\text{R}} = 400 \text{ V}; \text{ d}I_{\text{F}}/\text{d}t = 500 \text{ A}/\mu\text{s}; \\ T_{j} = 100 ^{\circ}\text{C} $ | -   | 32  | 40   |
|                    |                                     | $I_F = 1 \text{ A};  \text{V}_\text{R} = 30  \text{V};  \text{d}_\text{F}/\text{d}\text{t} = 50  \text{A}/\mu\text{s}; \\ \text{T}_j = 25 \ ^\circ\text{C}$ | -   | 30  | 52   |
|                    |                                     | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$   | -   | 19  | -    |

T<sub>i</sub> = 25 °C; <u>Fig. 5</u>

# 5. Pinning information

| Table 2. | Pinning in | formation               |                    |                |
|----------|------------|-------------------------|--------------------|----------------|
| Pin      | Symbol     | Description             | Simplified outline | Graphic symbol |
| 1        | К          | cathode                 | mb                 | K – K – A      |
| 2        | А          | anode                   |                    | 001aaa020      |
| mb       | n.c.       | mounting base; isolated | TO-220F (SOD113)   |                |

# 6. Ordering information

| Table 3. Ordering information |         |   |         |  |  |  |  |
|-------------------------------|---------|---|---------|--|--|--|--|
| Type number                   | Package |   |         |  |  |  |  |
|                               | Name    | Description   | Version |  |  |  |  |
| BYC8X-600                     | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack" | SOD113  |  |  |  |  |

## 7. Marking

### Table 4. Marking codes

| Type number | Marking codes |
|-------------|---------------|
| BYC8X-600   | BYC8X         |
|             | 600           |

## 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                       | Conditions   | Min | Max | Unit |
|--------------------|---------------------------------|--|-----|-----|------|
| V <sub>RRM</sub>   | repetitive peak reverse voltage |  | -   | 600 | V    |
| V <sub>RWM</sub>   | crest working reverse voltage   |  | -   | 600 | V    |
| I <sub>F(AV)</sub> | average forward current         | δ = 0.5 ; T <sub>h</sub> ≤ 59 °C; square-wave pulse;<br>Fig. 1; Fig. 2         | -   | 8   | A    |
| I <sub>FRM</sub>   | repetitive peak forward current | $\delta$ = 0.5 $\ ; t_p$ = 25 µs; $T_h \leq \ 59 \ ^\circ C;$ squarewave pulse | -   | 16  | A    |
| I <sub>FSM</sub>   | non-repetitive peak             | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                          | -   | 80  | А    |
|                    | forward current                 | t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; sine-wave<br>pulse      | -   | 88  | A    |
| T <sub>stg</sub>   | storage temperature             |  | -40 | 150 | °C   |
| Tj                 | junction temperature            |  | -   | 150 | °C   |

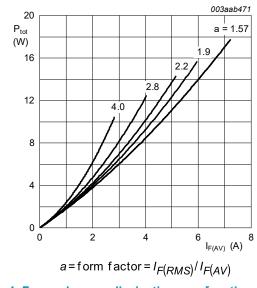


Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

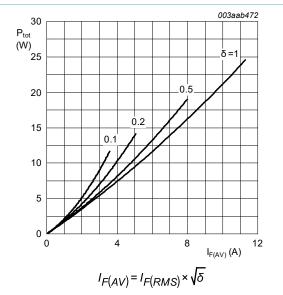


Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

Hyperfast power diode

## 9. Thermal characteristics

| Symbol               | Parameter  | Conditions                     | Min | Тур | Max | Unit |
|----------------------|--|--------------------------------|-----|-----|-----|------|
| R <sub>th(j-h)</sub> | thermal resistance<br>from junction to<br>heatsink         | with heatsink compound; Fig. 3 | -   | -   | 4.8 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance<br>from junction to<br>ambient free air |                                | -   | 55  | -   | K/W  |

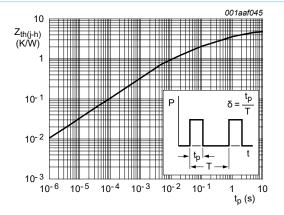


Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse width

## **10.** Isolation characteristics

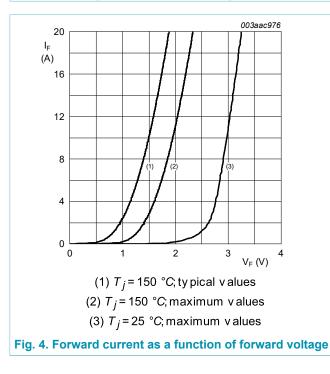
| Table 7. Isolati       | on characteristics    |   |     |     |      |      |
|------------------------|-----------------------|---|-----|-----|------|------|
| Symbol                 | Parameter             | Conditions  | Min | Тур | Max  | Unit |
| V <sub>isol(RMS)</sub> | RMS isolation voltage | 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from<br>all pins to external heatsink; sinusoidal<br>waveform; clean and dust free | -   | -   | 2500 | V    |
| C <sub>isol</sub>      | isolation capacitance | from cathode to external heatsink   | -   | 10  | -    | pF   |

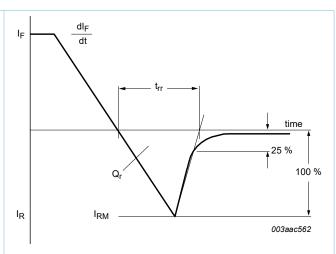
## Table 7 location observatoristi

Hyperfast power diode

## **11. Characteristics**

| Symbol          | Parameter                     | Conditions  | Mi    | n Typ   | Max  | Unit |
|-----------------|-------------------------------|---|-------|---------|------|------|
| Static chara    | cteristics                    |   |       |         |      |      |
| V <sub>F</sub>  | forward voltage               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>  | -     | 1.4     | 1.85 | V    |
|                 |                               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C  | -     | 2       | 2.9  | V    |
|                 |                               | I <sub>F</sub> = 16 A; T <sub>j</sub> = 150 °C  | -     | 1.7     | 2.3  | V    |
| I <sub>R</sub>  | reverse current               | V <sub>R</sub> = 500 V; T <sub>j</sub> = 100 °C   | -     | 1.1     | 3    | mA   |
|                 |                               | V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C  | -     | 9       | 150  | μA   |
| Dynamic ch      | aracteristics                 |   | · · · | · · · · |      |      |
| t <sub>rr</sub> | reverse recovery time         | $I_F$ = 8 A; $V_R$ = 400 V; $dI_F/dt$ = 500 A/µs; $T_j$ = 100 °C  | -     | 32      | 40   | ns   |
|                 |                               | $I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 50 A/µs; $T_j$ = 25 °C   | -     | 30      | 52   | ns   |
|                 |                               | $    I_F = 8 \text{ A}; \text{ V}_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \\    T_j = 25 \text{ °C}; \underline{\text{Fig. 5}} $ | -     | 19      | -    | ns   |
|                 | peak reverse recovery current | $I_F$ = 10 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/<br>µs; T <sub>j</sub> = 100 °C   | -     | 9.5     | 12   | A    |
|                 |                               | $I_{F}$ = 8 A; $V_{R}$ = 400 V; $dI_{F}/dt$ = 50 A/µs; $T_{j}$ = 125 °C   | -     | 1.5     | 5.5  | A    |
| Q <sub>r</sub>  | recovered charge              | $I_{F}$ = 1 A; $V_{R}$ = 100 V; $dI_{F}/dt$ = 100 A/µs; $T_{j}$ = 25 °C   | -     | 12      | -    | nC   |
| V <sub>FR</sub> | forward recovery voltage      | I <sub>F</sub> = 10 A; dI <sub>F</sub> /dt = 100 A/µs; T <sub>j</sub> = 25 °C;<br>Fig. 6  | -     | 8       | 10   | V    |





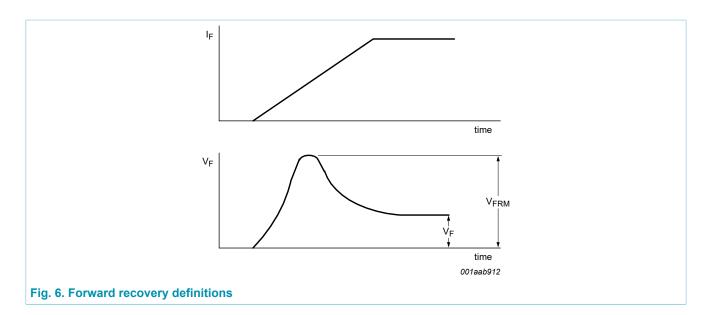
### Fig. 5. Reverse recovery definitions; ramp recovery

#### BYC8X-600

## WeEn Semiconductors

# **BYC8X-600**

### Hyperfast power diode

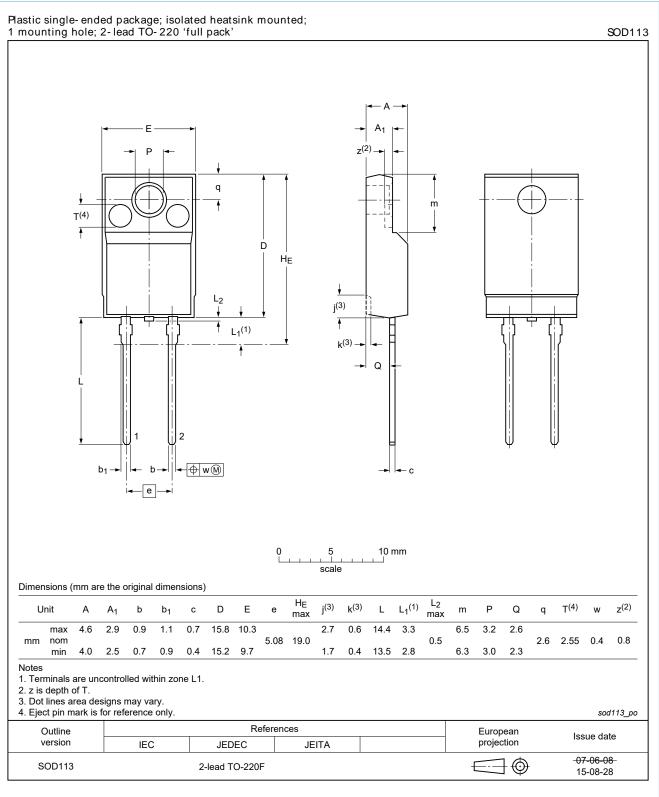


BYC8X-600



Hyperfast power diode

## **12. Package outline**



### Fig. 7. Package outline TO-220F (SOD113)

BYC8X-600

# BYC8X-600

#### Hyperfast power diode

## 13. Legal information

#### **Data sheet status**

| Document<br>status [1][2]            | Product<br>status [ <u>3]</u> | Definition  |
|--------------------------------------|-------------------------------|---|
| Objective<br>[short] data<br>sheet   | Development                   | This document contains data from<br>the objective specification for product<br>development. |
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